

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

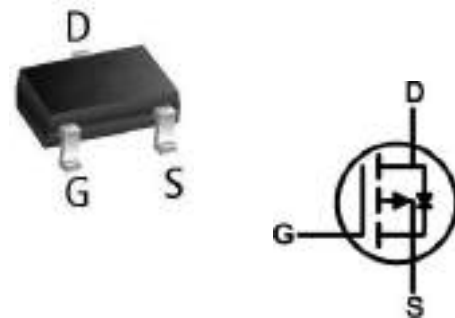
## Product Summary

BVDSS	R <sub>DS(on)</sub>	I <sub>D</sub>
-18V	19mΩ	-7.0A

## Description

The TCS1187 is the high cell density trenched P-ch MOSFETs, which provides excellent R<sub>DS(on)</sub> and efficiency for most of the small power switching and load switch applications. The TCS1187 meet the RoHS and Green Product requirement with full function reliability approved.

## SOT 23 Pin Configurations



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	-18	V
V <sub>GS</sub>	Gate-Source Voltage	±12	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ -4.5V <sup>1</sup>	-7.0	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ -4.5V <sup>1</sup>	-4.8	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	-18.8	A
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>3</sup>	1.9	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-ambient <sup>1</sup>	---	65	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	80	°C/W